

# Dual P-CHANNEL MOSFET

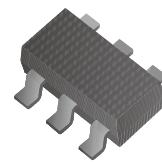
**Comchip**  
SMD Diode Specialist

## CMS02P02T6-HF

### Dual P-CHANNEL MOSFET

RoHS Device

Halogen Free



### Features

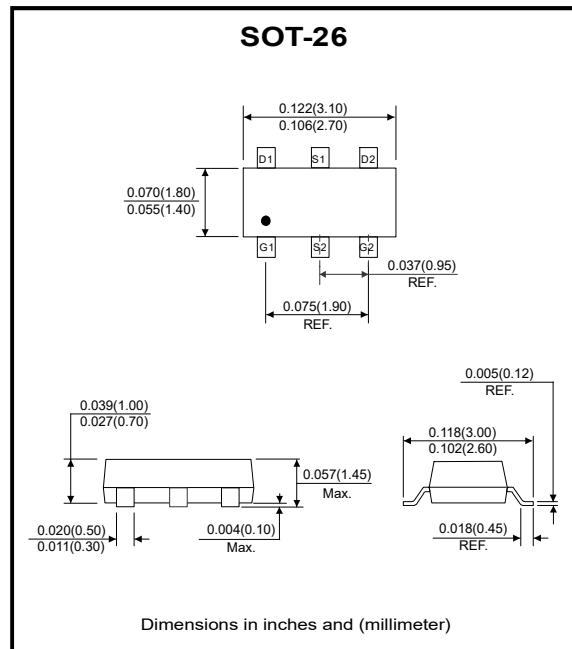
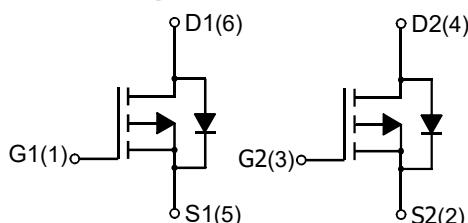
- Advanced DMOS Trench technology
- Fast Switching
- Suit for 1.8V Gate Drive Applications
- Green Device Available

### Description

The CMS02P02T6 is using trench DMOS technology. This advanced technology has been especially tailored to minimize  $R_{DS(ON)}$ , provide superior switching performance. These devices are well suited for high efficiency fast switching applications.

The CMS02P02T6 meet the RoHS and Green Product requirement with full function reliability approved.

### Circuit diagram



### Absolute Maximum Ratings (at $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current <sup>1</sup>	$I_D @ T_C=25^\circ\text{C}$	-2.5	A
Continuous Drain Current <sup>1</sup>	$I_D @ T_C=100^\circ\text{C}$	-1.5	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-10	A
Power Dissipation <sup>3</sup>	$P_D @ T_C=25^\circ\text{C}$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 ~ +150	°C

### Thermal Data

Parameter	Symbol	Max. Ratings	Unit
Thermal Resistance Junction-ambient <sup>1</sup>	$R_{\theta JA}$	100	°C/W

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## Electrical Characteristics (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =-250uA
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.3	-0.6	-1.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA
Gate-Source Leakage Current	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±10V
Drain-Source Leakage Current(T <sub>J</sub> =25°C)	I <sub>DSS</sub>	-	-	-1	uA	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0
Drain-Source Leakage Current(T <sub>J</sub> =125°C)		-	-	-10		V <sub>DS</sub> =-16V, V <sub>GS</sub> =0
Static Drain-Source On-Resistance <sup>2</sup>	R <sub>DS(ON)</sub>	-	-	90	mΩ	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.5A
		-	-	130		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.0A
		-	-	180		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-1.0A
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	-	4.8	-	nC	I <sub>D</sub> =-2A V <sub>DS</sub> =-10V V <sub>GS</sub> =-4.5V
Gate-Source Charge	Q <sub>gs</sub>	-	0.5	-		
Gate-Drain ("Miller") Change	Q <sub>gd</sub>	-	1.9	-		
Turn-on Delay Time <sup>2</sup>	T <sub>d(on)</sub>	-	3.5	-	ns	V <sub>DS</sub> =-10V I <sub>D</sub> =-1A V <sub>GS</sub> =-4.5V R <sub>G</sub> =25Ω
Rise Time	T <sub>r</sub>	-	12.6	-		
Turn-off Delay Time	T <sub>d(off)</sub>	-	32.6	-		
Fall Time	T <sub>f</sub>	-	8.4	-		
Input Capacitance	C <sub>iss</sub>	-	350	-	pF	V <sub>GS</sub> =0V V <sub>DS</sub> =-15V f=1.0MHz
Output Capacitance	C <sub>oss</sub>	-	66	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	50	-		

### Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Diode Forward Voltage <sup>2</sup>	V <sub>SD</sub>	-	-	-1.0	V	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C
Continuous Source Current <sup>1,4</sup>	I <sub>S</sub>	-	-	-2.5	A	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current
Pulsed Source Current <sup>2,4</sup>	I <sub>SM</sub>	-	-	-5.0	A	

Notes: 1. Surface mounted on a 1 inch <sup>2</sup> FR-4 board with 2OZ copper.

2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. The power dissipation is limited by 150°C junction temperature.
4. The data is theoretically the same as ID and IDM , in real applications, should be limited by total power dissipation.

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## RATING AND CHARACTERISTIC CURVES

### Typical characteristics

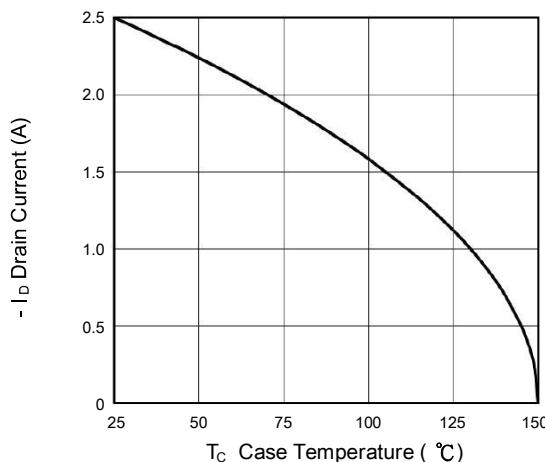


Fig.1 Drain Current vs. T<sub>C</sub>

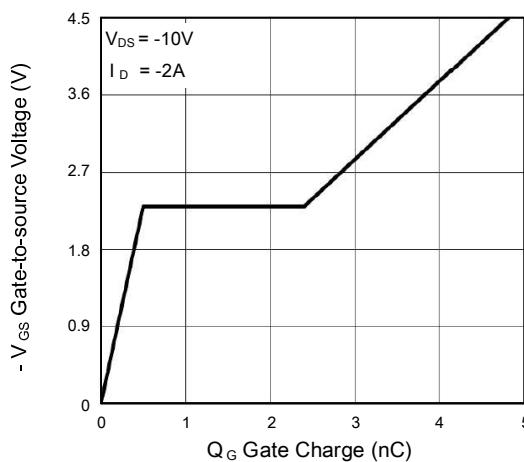


Fig.2 Gate Charge Characteristics

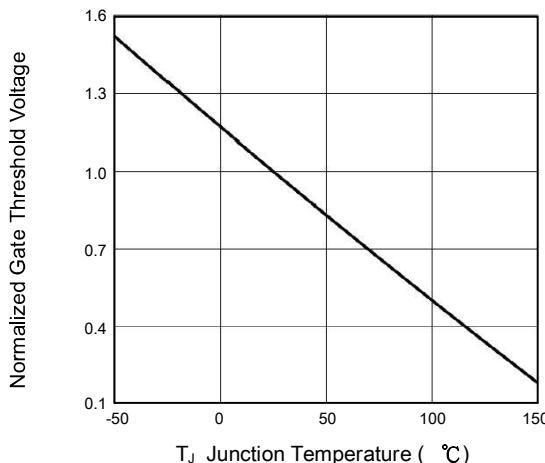


Fig.3 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

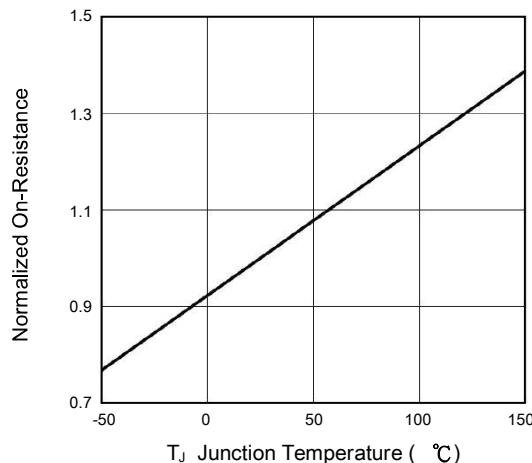


Fig.4 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>

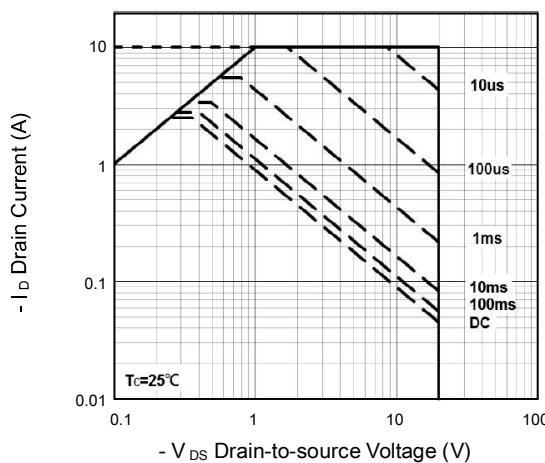


Fig.5 Safe Operating Area

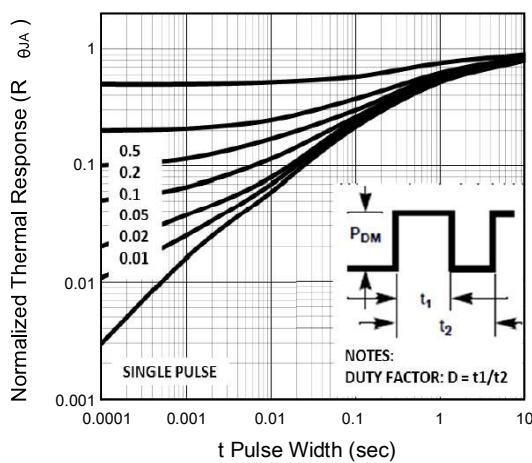


Fig.6 Transient Thermal Impedance

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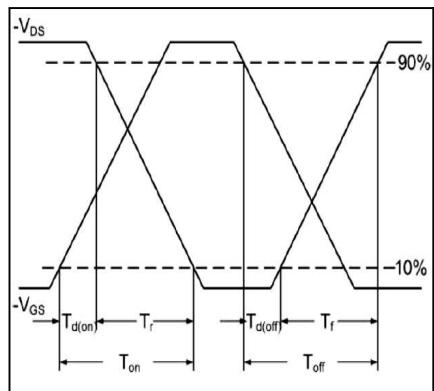


Fig.7 Switching Time Waveform

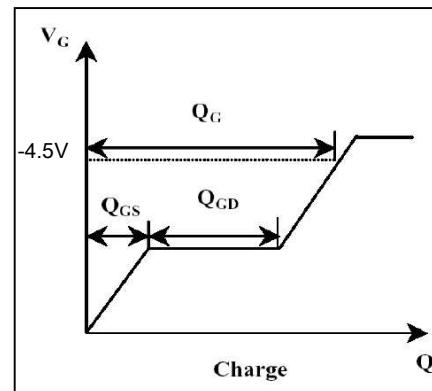
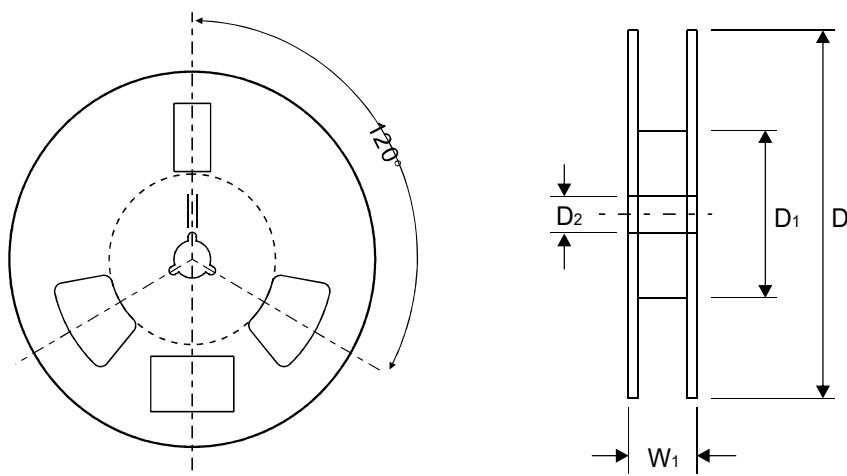
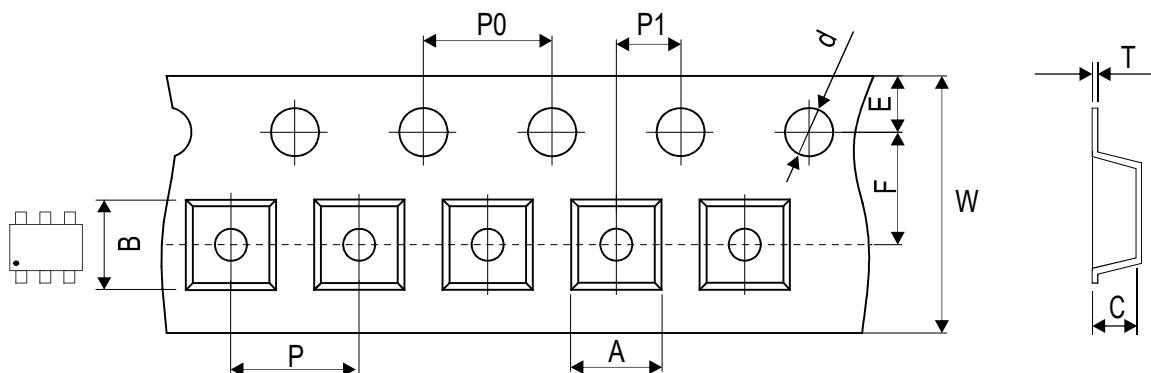


Fig.8 Gate Charge Waveform

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## Reel Taping Specification



SOT-26	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	$3.17 \pm 0.10$	$3.10 \pm 0.10$	$1.10 \pm 0.10$	$1.50 + 0.10$ - 0.00	$180.00 + 0.00$ - 3.00	$60.00 \pm 0.50$	$13.00 \pm 0.20$
	(inch)	$0.125 \pm 0.004$	$0.122 \pm 0.004$	$0.043 \pm 0.004$	$0.059 + 0.001$ - 0.00	$7.087 + 0.00$ - 0.118	$2.362 \pm 0.020$	$0.512 \pm 0.008$

SOT-26	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	$1.75 \pm 0.10$	$3.50 \pm 0.10$	$4.00 \pm 0.10$	$4.00 \pm 0.10$	$2.00 \pm 0.05$	$0.25 \pm 0.03$	$8.00 + 0.30$ - 0.10	$12.30 + 1.00$ - 0.30
	(inch)	$0.069 \pm 0.004$	$0.138 \pm 0.004$	$0.157 \pm 0.004$	$0.157 \pm 0.004$	$0.079 \pm 0.002$	$0.010 \pm 0.001$	$0.315 + 0.012$ - 0.004	$0.484 + 0.039$ - 0.012

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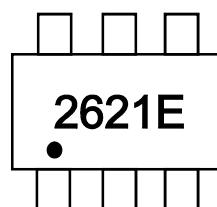
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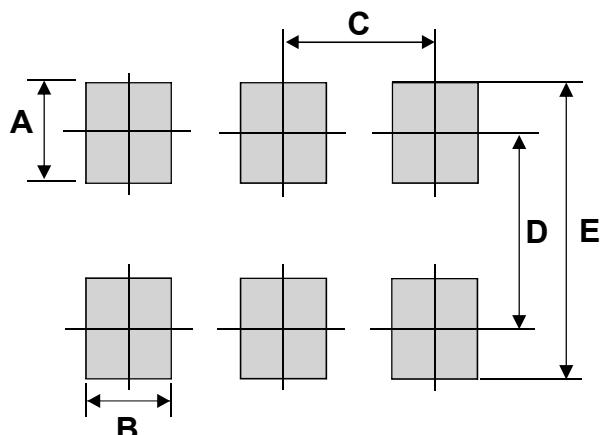
### Marking Code

Part Number	Marking Code
CMS02P02T6-HF	2621E



### Suggested PAD Layout

SIZE	TSOP-6	
	(mm)	(inch)
A	1.00 Min	0.039 Min
B	0.70 Min	0.028 Min
C	0.95 Min	0.037Min
D	2.40 Min	0.094Min
E	3.40 Min	0.134 Min



### Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
SOT-26	3,000	7

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